

Vorläufige Daten Preliminary Data

Diode, Wechselrichter / Diode, Inverter Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzensperrspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
Dauergleichstrom Continuous DC forward current		I_F	25	A
Periodischer Spitzenstrom Repetitive peak forward current	$t_p = 1\text{ ms}$	I_{FRM}	50	A
Grenzlastintegral I^2t - value	$V_R = 0\text{ V}, t_p = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_p = 10\text{ ms}, T_{vj} = 175^{\circ}\text{C}$	I^2t	72,5 63,0	A^2s A^2s

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	$I_F = 25\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 25\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 25\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	V_F	1,83 1,70 1,63	t.b.d.	V V V
Rückstromspitze Peak reverse recovery current	$I_F = 25\text{ A}, -di_F/dt = 950\text{ A}/\mu\text{s} (T_{vj}=175^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	I_{RM}	24,2 32,4 37,6		A A A
Sperrverzögerungsladung Recovered charge	$I_F = 25\text{ A}, -di_F/dt = 950\text{ A}/\mu\text{s} (T_{vj}=175^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	Q_r	2,25 3,82 4,95		μC μC μC
Abschaltenergie pro Puls Reverse recovery energy	$I_F = 25\text{ A}, -di_F/dt = 950\text{ A}/\mu\text{s} (T_{vj}=175^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	E_{rec}	0,65 1,41 1,87		mJ mJ mJ
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro Diode / per diode		R_{thJH}	2,04		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{ op}}$	-40	175	$^{\circ}\text{C}$

Diode, Gleichrichter / Diode, Rectifier Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzensperrspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1600	V
Durchlassstrom Grenzeffektivwert pro Chip Maximum RMS forward current per chip	$T_H = 100^{\circ}\text{C}$	I_{FRMSM}	25	A
Gleichrichter Ausgang Grenzeffektivstrom Maximum RMS current at rectifier output	$T_H = 100^{\circ}\text{C}$	I_{RMSM}	25	A
Stoßstrom Grenzwert Surge forward current	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I_{FSM}	300 245	A A
Grenzlastintegral I^2t - value	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	450 300	A^2s A^2s

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	$T_{vj} = 150^{\circ}\text{C}, I_F = 10\text{ A}$	V_F		0,80		V
Sperrstrom Reverse current	$T_{vj} = 150^{\circ}\text{C}, V_R = 1600\text{ V}$	I_R		1,00		mA
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro Diode / per diode		R_{thJH}	1,54		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

IGBT, Brems-Chopper / IGBT, Brake-Chopper

Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
Kollektor-Dauergleichstrom Continuous DC collector current	$T_H = 60^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	I_{CDC}	25	A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	50	A
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

			min.	typ.	max.		
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 25\text{ A}$ $V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	$V_{CE\text{ sat}}$	1,60 1,74 1,82	t.b.d.	V V V	
Gate-Schwellenspannung Gate threshold voltage	$I_C = 0,525\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,15	5,80	6,45	V
Gateladung Gate charge	$V_{GE} = -15 / 15\text{ V}, V_{CE} = 600\text{ V}$		Q_G	0,395			μC
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	0,0			Ω
Eingangskapazität Input capacitance	$f = 100\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	4,77			nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 100\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,017			nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		0,0056		mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		100		nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 10\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	t_{don}	0,058 0,06 0,061			μs μs μs
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 10\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	t_r	0,055 0,057 0,058			μs μs μs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 10\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	t_{doff}	0,20 0,28 0,38			μs μs μs
Fallzeit, induktive Last Fall time, inductive load	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 10\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	t_f	0,18 0,29 0,35			μs μs μs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}, L\sigma = 35\text{ nH}$ $di/dt = 320\text{ A}/\mu\text{s} (T_{vj} = 175^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Gon} = 10\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	E_{on}	2,15 2,65 2,90			mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}, L\sigma = 35\text{ nH}$ $du/dt = 2700\text{ V}/\mu\text{s} (T_{vj} = 175^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Goff} = 10\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	E_{off}	2,10 3,05 3,65			mJ mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$	$t_P \leq 8\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$ $t_P \leq 7\ \mu\text{s}, T_{vj} = 175^{\circ}\text{C}$	I_{SC}	80 75			A A
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro IGBT / per IGBT		R_{thJH}	1,55			K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{ op}}$	-40	175		$^{\circ}\text{C}$